

SANYO	No.2112B	2SB1201/2SD1801
	PNP/NPN Epitaxial Planar Silicon Transistors High-Current Switching Applications	

Applications

- Voltage regulators, relay drivers, lamp drivers, electrical equipment

Features

- Adoption of FBET, MBIT processes
- Large current capacity and wide ASO
- Low collector-to-emitter saturation voltage
- Fast switching speed
- Small and slim package making it easy to make 2SB1201/2SD1801-used sets smaller

() : 2SB1201

Absolute Maximum Ratings at Ta = 25°C

			unit
Collector to Base Voltage	V _{CBO}	(-)	60 V
Collector to Emitter Voltage	V _{CEO}	(-)	50 V
Emitter to Base Voltage	V _{EBO}	(-)	6 V
Collector Current	I _C	(-)	2 A
Collector Current(Pulse)	I _{CP}	(-)	4 A
Collector Dissipation	P _C		0.8 W
		T _c = 25°C	15 W
Junction Temperature	T _j		150 °C
Storage Temperature	T _{stg}		- 55 to + 150 °C

Electrical Characteristics at Ta = 25°C

			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} = (-)50V, I _E = 0			(-)	100 nA
Emitter Cutoff Current	I _{EBO}	V _{EB} = (-)4V, I _C = 0			(-)	100 nA
DC Current Gain	h _{FE} (1)	V _{CE} = (-)2V, I _C = (-)100mA	100*		560*	
	h _{FE} (2)	V _{CE} = (-)2V, I _C = (-)1.5A	40			
Gain-Bandwidth Product	f _T	V _{CE} = (-)10V, I _C = (-)50mA		150		MHz
Output Capacitance	c _{ob}	V _{CE} = (-)10V, f = 1MHz		(22)12		pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = (-)1A, I _B = (-)50mA		0.15	0.4	V
				(-0.3)	(-0.7)	

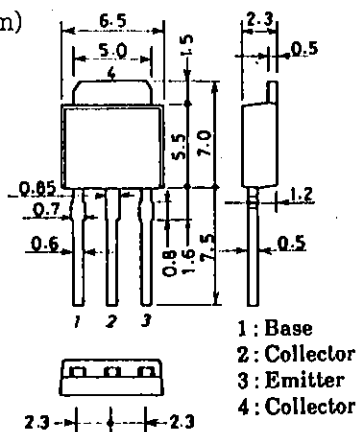
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* : The 2SB1201/2SD1801 are classified by 100mA h_{FE} as follows :

100 R 200	140 S 280	200 T 400	280 U 560
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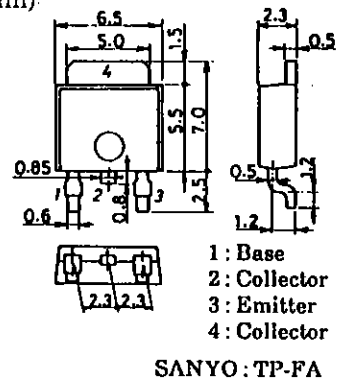
Package Dimensions 2045B

(unit : mm)



Package Dimensions 2044B

(unit : mm)

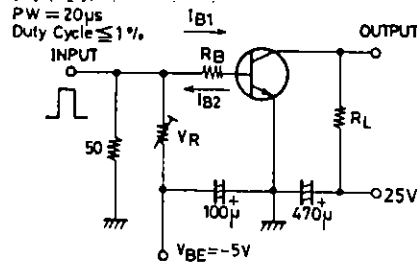


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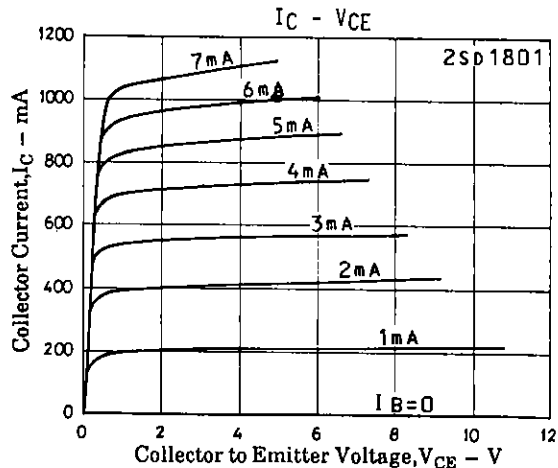
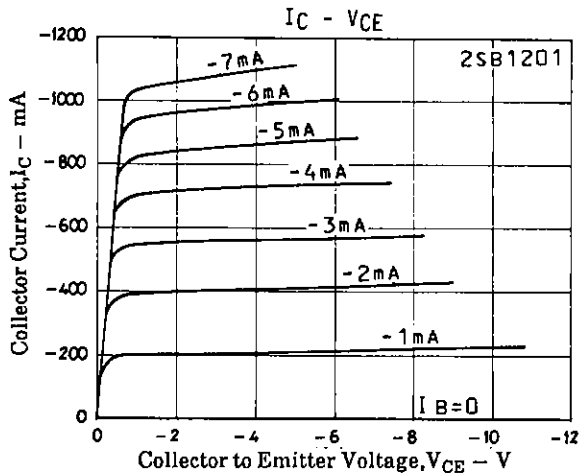
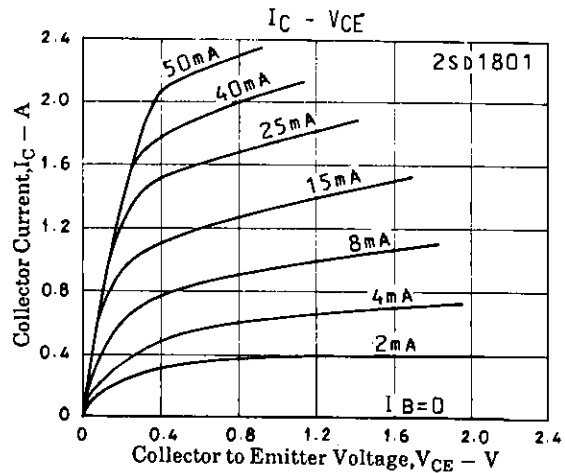
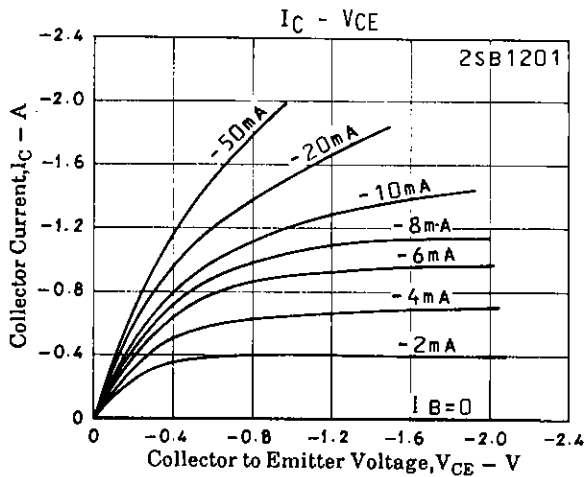
			min	typ	max	unit
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C = (-)1A, I_B = (-)50mA$		(-)0.9	(-)1.2	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu A, I_E = 0$	(-)60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1mA, R_{BE} = \infty$	(-)50			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu A, I_C = 0$	(-)6			V
Turn-on Time	t_{on}	See specified Test Circuit.		60		ns
Storage Time	t_{stg}			(450)550		ns
Fall Time	t_f			30		ns

Switching Time Test Circuit

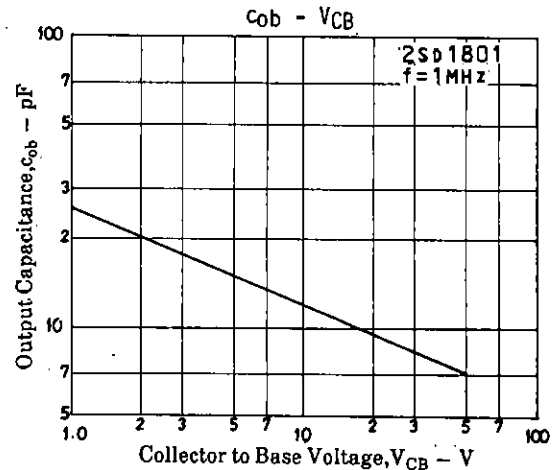
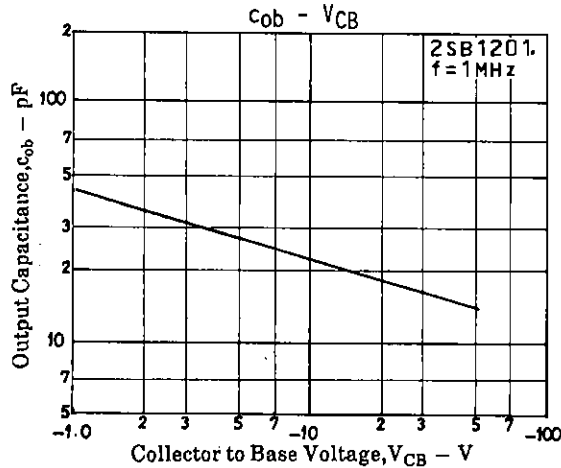
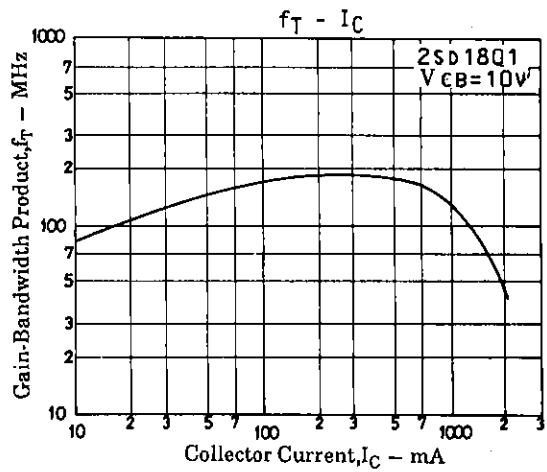
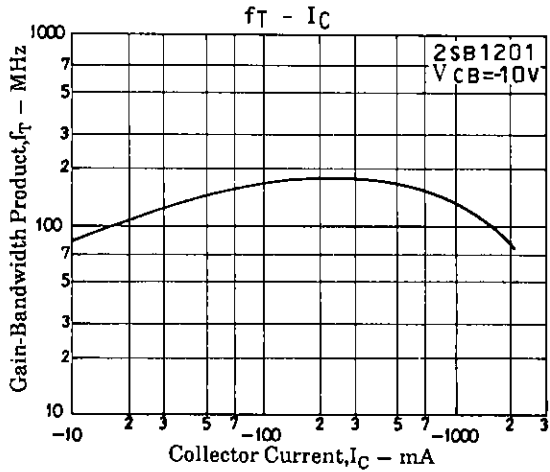
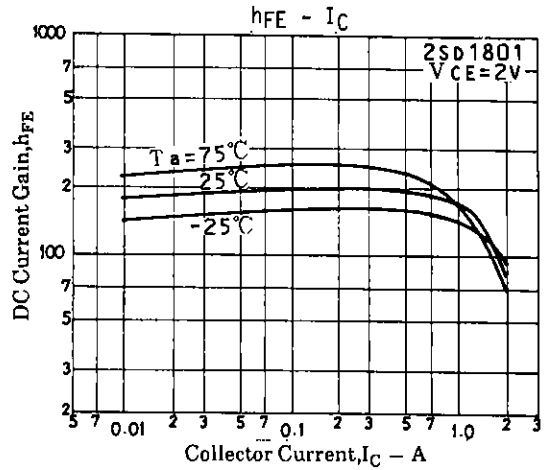
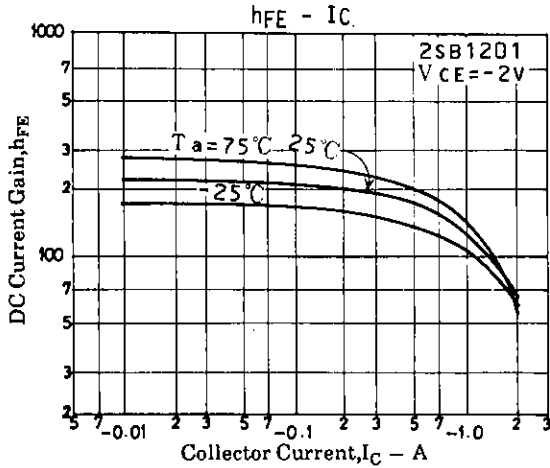
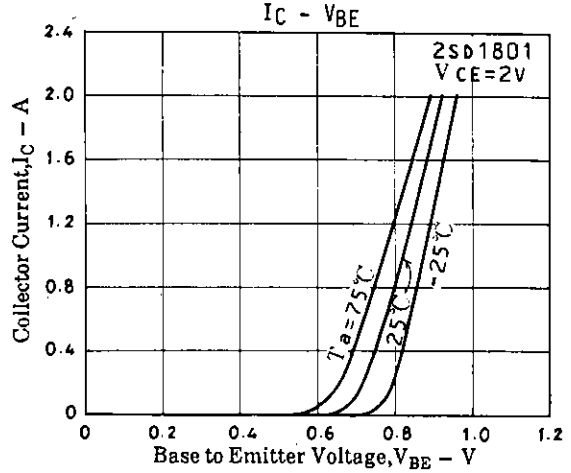
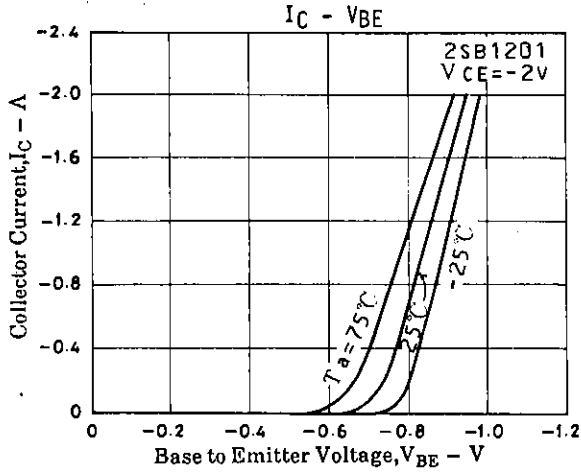


$I_C = 10 I_B = -10 I_{B2} = 500mA, V_{CC} = 25V$
(For PNP, the polarity is reversed.)

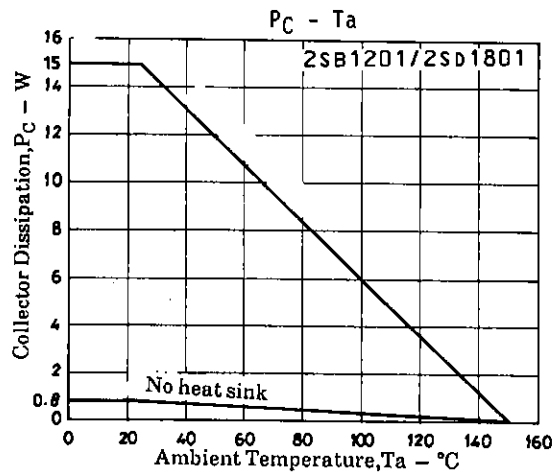
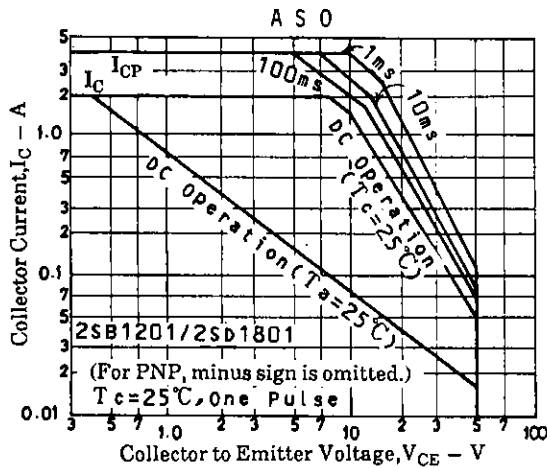
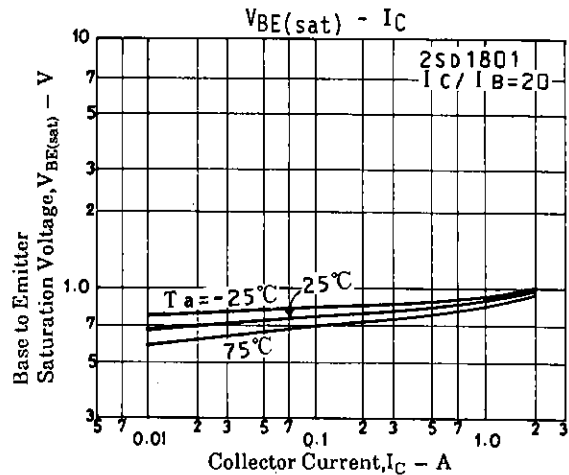
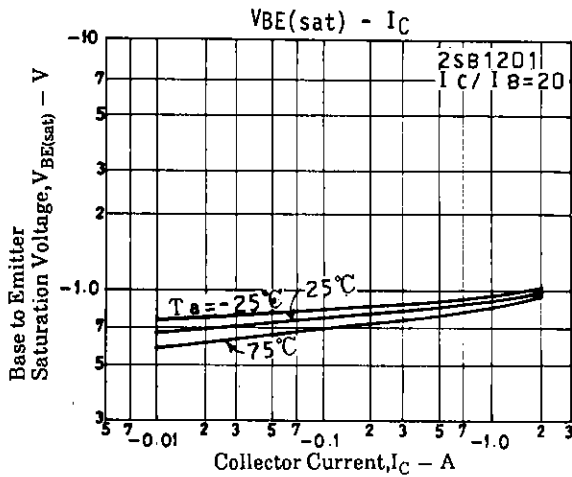
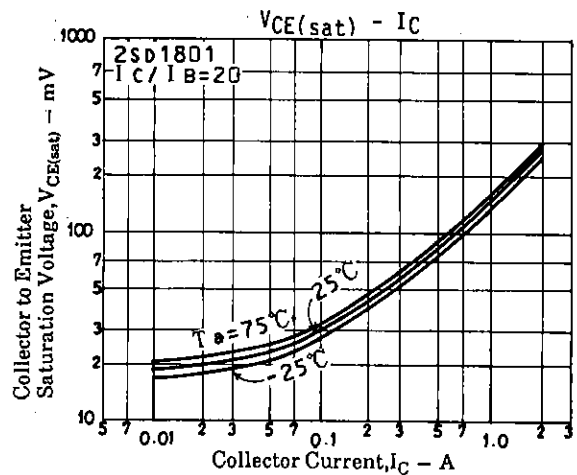
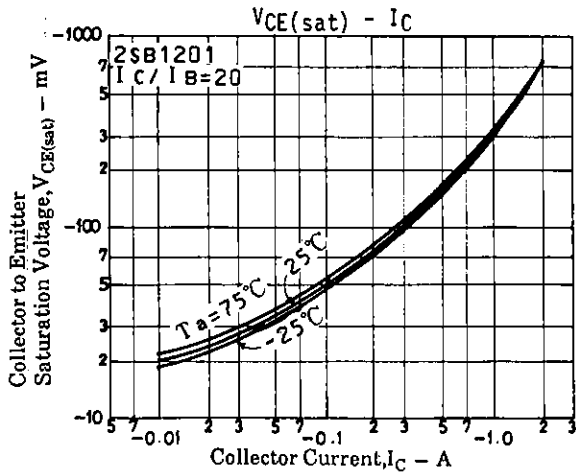
Unit (Resistance : Ω , Capacitance : F)



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